

### CMOS 2V/3V/5VLowRonSPDTSwitch

## **Preliminary Technical Data**

**ADG719** 

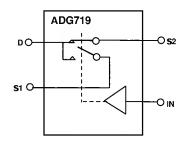
**FEATURES** 

+1.8Vto 5.5V Single Supply  $2\Omega$  On Resistance Bandwidth 100MHz Rail to Rail Operation Very Low Distortion 6-lead SOT-23, 8-lead  $\mu$ SOIC Packages Fast Switching Times  $t_{ON}$  20 ns  $t_{OFF}$  10 ns

Low Power Consumption (1µW) TTL/CMOS Compatible

APPLICATIONS
Battery Powered Systems
Communication Systems
Sample Hold Systems
Audio Signal Routing
Mechanical Reed Relay Replacement

#### FUNCTIONAL BLOCK DIAGRAM



#### GENERAL DESCRIPTION

The ADG719 is a monolithic CMOS SPDT switch. This switch is designed on a sub-micron process which provides low power dissipitation yet gives high switching speed, low on resistance and low leakage currents.

The ADG719 can operate from a single supply range of +1.8V to +5.5V making it ideal for use in battery powered instruments, and with the new generation of DACs and ADCs from Analog Devices.

Each switch of the ADG719 conducts equally well in both directions when ON. The ADG719 exhibits break before make switching action.

The ADG719 is available in 6-lead SOT-23 package, and 8-Lead  $\mu SOIC.$ 

#### PRODUCT HIGHLIGHTS

- 1. +2V/+3V/+5V Single Supply Operation. The ADG719 offers high performance, including low on resistance and fast switching times and is fully specified and guaranteed with +3V and +5V supply rails.
- 2. Low  $R_{ON}\ (2\Omega$  ).
- 3. Bandwidth 100MHz
- 4. Low power dissipation

  CMOS construction ensures low power dissipation.
- 5. Fast  $T_{ON}/T_{OFF}$
- 6. Tiny 6-lead SOT-23 and 8-lead μSOIC.

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## Preliminary Technical Data ADG719—SPECIFICATIONS<sup>1</sup>

(V<sub>DD</sub> = 5V  $\pm$  10%, GND = 0 V. All specifications -40°C to +85°C, unless otherwise noted.)

	B Version -40°C to		
Parameter	+25°C +85°C	Units	Test Conditions/Comments
ANALOG SWITCH			
Analog Signal Range	0 V to V <sub>DD</sub>		V
On-Resistance (R <sub>ON)</sub>	2	Ω typ	$V_S = 0V$ to $5V$
	5	Ω max	
On-Resistance Match Between			
Channels ( $\Delta R_{ON}$ )		Ω typ	
	1.0	Ω max	
On-Resistance Flatness (R <sub>FLAT(ON)</sub> )	1.0		$\Omega$ typ
	1.0	Ω max	
LEAKAGE CURRENTS			TBD
Source OFF Leakage I <sub>S</sub> (OFF)		nA typ	
	2.0	nA max	
Drain OFF Leakage I <sub>D</sub> (OFF)		nA typ	
	2.0	nA max	
Channel ON Leakage I <sub>D</sub> , I <sub>S</sub> (ON)		nA typ	
	4.0	nA max	
DIGITAL INPUTS			
Input High Voltage, V <sub>INH</sub>	2.4	V min	
Input Low Voltage, V <sub>INL</sub>	0.8	V max	
Input Current			
$I_{INL}$ or $I_{INH}$	0.005	μA typ	$V_{IN} = V_{INL}$ or $V_{INH}$
	±0.5	μA max	
DYNAMIC CHARACTERISTICS <sup>2</sup>			
ton	20	ns max	TBD
toff	10	ns max	122
-011			
Break-Before-Make Time Delay, $t_D$	1 1	ns min	
Channel-to-Channel Crosstalk	85	dB typ	
B 1 111 01B	100	,	
Bandwidth - 3dB	100	MHz typ	
Bandwidth ± 0.1 dB	TBD	MHz typ	
Off Isolation	80	dB typ	
C <sub>s</sub> (OFF)	TBD	pF typ	
$C_{\rm D}$ (OFF)	TBD	pF typ	
$C_D, C_S (ON)$	TBD	pF typ	
POWER REQUIREMENTS		I -01	V <sub>DD</sub> = +5 V
10 "DIC REQUIREMENTS			$V_{DD} = +3$ V Digital Inputs = 0 V or 5 V
Ipp	0.0001	μΑ tvp	0
טוט	I .		
${ m I}_{ m DD}$	0.0001	μΑ typ μΑ max	

NOTES <sup>1</sup>Temperature ranges are as follows: B Versions: -40°C to +85°C.

<sup>&</sup>lt;sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

# Preliminary Technical Data ADG719—SPECIFICATIONS<sup>1</sup>

 $\begin{tabular}{lll} ADG719 \\ (V_{DD}=2.7V\ to\ 3.6V, & GND=0\ V.\ All\ specifications\ -40^{\circ}C\ to\ +85^{\circ}C, unless\ other-all\ specifications\ -40^{\circ}C\$ erwise noted.)

	B Ver	sion –40°C to		
Parameter	+25°C	+85 ° C	Units	Test Conditions/Comments
ANALOG SWITCH Analog Signal Range On-Resistance (R <sub>ON)</sub>		0 V to V <sub>DD</sub> 2 8	Ω typ Ω max	$V$ $V_S = 0V$ to $3V$
On-Resistance Match Between Channels ( $\Delta R_{\rm ON}$ ) On-Resistance Flatness ( $R_{\rm FLAT(ON)}$ )		1.0	Ω typ Ω max	$\Omega$ typ
		2.0	Ω max	
LEAKAGE CURRENTS Source OFF Leakage $I_S$ (OFF)  Drain OFF Leakage $I_D$ (OFF)  Channel ON Leakage $I_D$ , $I_S$ (ON)		2.0 2.0 4.0	nA typ nA max nA typ nA max nA typ nA max	TBD
DIGITAL INPUTS Input High Voltage, $V_{INH}$ Input Low Voltage, $V_{INL}$ Input Current $I_{INL}$ or $I_{INH}$	0.005	2.0 0.4	V min V max μΑ typ	$V_{\rm IN}$ = $V_{\rm INL}$ or $V_{\rm INH}$
$\begin{array}{c} \hline \\ DYNAMIC & CHARACTERISTICS^2 \\ t_{ON} \\ t_{OFF} \end{array}$		±0.5 30 15	μA max ns max ns max	TBD
Break-Before-Make Time Delay, t <sub>D</sub>	1	1	ns min	
Channel-to-Channel Crosstalk	85		dB typ	
Bandwidth - 3dB Bandwidth ± 0.1 dB	110 TBD		MHz typ	
Off Isolation  C <sub>S</sub> (OFF)  C <sub>D</sub> (OFF)  C <sub>D</sub> , C <sub>S</sub> (ON)	80 TBD TBD TBD		dB typ pF typ pF typ pF typ	
$\overline{POWER REQUIREMENTS}$ $I_{DD}$	0.0001		μA typ	$V_{DD}$ = +3 V Digital Inputs = 0 V or 3 V
		0.5	μA max	

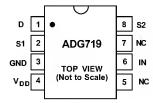
<sup>&</sup>lt;sup>1</sup>Temperature ranges are as follows: B Versions: -40°C to +85°C.

<sup>&</sup>lt;sup>2</sup>Guaranteed by design, not subject to production test.

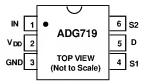
 $Specifications \, subject \, to \, change \, without \, notice.$ 

### **Preliminary Technical Data**

### PIN CONFIGURATION (MICRO SOIC)



### PIN CONFIGURATION (SOT-23)



### ABSOLUTE MAXIMUM RATINGS1

(T<sub>A</sub> = +25°C unless otherwise noted)

V <sub>DD</sub> to GND	+ / V
Analog, Digital Inputs $^2$ $\dots$ $-0.3 V$ to $V_{DD}$ +0.3 $$ 30 mA, Whichever Occurs	

30 mA, Whichever Occurs First
(Pulsed at 1 ms, 10% Duty Cycle max)
Operating Temperature Range
Industrial (B Version)40°C to +85°C
Storage Temperature Range65°C to +150°C
Junction Temperature+150°C
microSOIC Package, Power Dissipation 450 mW
$\theta_{JA}$ Thermal Impedance
θ <sub>IC</sub> Thermal Impedance
Lead Temperature, Soldering
Vapor Phase (60 sec) +215°C
Infrared (15 sec)+220°C
SOT-23 Package, Power Dissipation TBD mW
θ <sub>IA</sub> Thermal Impedance
$\theta_{\text{IC}}$ Thermal Impedance
Lead Temperature, Soldering
Vapor Phase (60 sec)+215°C
Infrared (15 sec)+220°C
ESD 2kV

#### NOTES

### ORDERING GUIDE

Model <sup>1</sup> Temperature Range		Package Option <sup>1</sup>	
ADG719BRT	-40°C to +85°C	RT-6	
ADG719BRM	-40°C to +85°C	RM-8	

### **NOTES**

<sup>1</sup>RT = SOT-23; RM = microSOIC.

### CAUTION\_

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG719 feature proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

<sup>&</sup>lt;sup>1</sup>Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

<sup>&</sup>lt;sup>2</sup>Overvoltages at IN, S or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

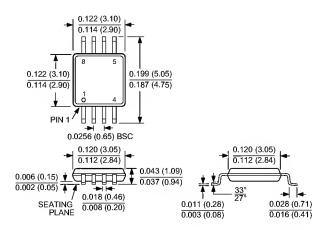
### **TERMINOLOGY**

$V_{DD}$	Most positive power supply potential.
GND	Ground (0 V) reference.
S	Source terminal. May be an input or output.
D	Drain terminal. May be an input or output.
IN	Logic control input.
$R_{ON}$	Ohmic resistance between D and S.
$\Delta R_{\rm ON}$	On resistance match between any two channels i.e. $R_{\rm ON} max$ - $R_{\rm ON} min$ .
R <sub>FLAT(ON)</sub>	Flatness is defined as the difference between the maximum and minimum value of on- resistance as measured over the specified analog signal range.
I <sub>S</sub> (OFF)	Source leakage current with the switch "OFF."
I <sub>D</sub> (OFF)	Drain leakage current with the switch "OFF."
$I_D$ , $I_S$ (ON)	Channel leakage current with the switch "ON."
$V_{D}(V_{S})$	Analog voltage on terminals D, S.
C <sub>S</sub> (OFF)	"OFF" switch source capacitance.
$C_D$ (OFF)	"OFF" switch drain capacitance.
$C_D$ , $C_S$ (ON	"ON" switch capacitance.
$t_{ON}$	Delay between applying the digital control input and the output switching on.
t <sub>OFF</sub>	Delay between applying the digital control input and the output switching off.
$t_{\mathrm{D}}$	"OFF" time or "ON" time measured between the 90% points of both switches, when switching from one address state to another.
Crosstalk	A measure of unwanted signal which is coupled through from one channel to another as a result of parasitic capacitance.
Off Isolation	A measure of unwanted signal coupling through an "OFF" switch.

#### MECHANICAL INFORMATION

Dimensions are shown in inches and (mm).

### 8-Pin microSOIC (RM-8)



### 6-Pin SOT23 (RT-6)

